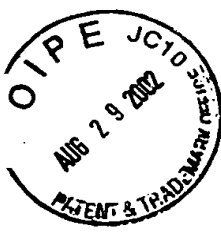


6/28/11

PATENT

Attorney's Docket No. 5308-156



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Ryu et al.
Serial No.: 09/911,995
Filed: July 24, 2001

Group Art Unit: 2811
Confirmation No.: 5240

For: SILICON CARBIDE POWER METAL-OXIDE SEMICONDUCTOR FIELD
EFFECT TRANSISTORS HAVING A SHORTING CHANNEL AND
METHODS OF FABRICATING SILICON CARBIDE METAL-OXIDE
SEMICONDUCTOR FIELD EFFECT TRANSISTORS HAVING A
SHORTING CHANNEL

Date: August 26, 2002

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FJ 10/05
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Commissioner for Patents
Washington, DC 20231

INFORMATION DISCLOSURE STATEMENT

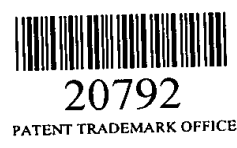
Sir:

Attached is a form PTO-1449, together with a copy of the identified document(s). This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(b), within three months of the filing date of the above-referenced application or before the mailing of a first Office Action on the merits, whichever event occurs last. Accordingly, no fee is required. The Commissioner is authorized to charge any additional fee, or credit any refund, to our Deposit Account No. 50-0220.

Respectfully submitted,

Timothy J. O'Sullivan
Registration No. 35,632

Customer Number:



CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Washington, DC 20231, on August 26, 2002.

Traci A. Brown
Date of Signature: August 26, 2002